MICROWAVE POWER GaAs FET TIM6472-60SL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 48.0dBm at 6.4GHz to 7.2GHz

·HIGH GAIN

G1dB= 7.5dB at 6.4GHz to 7.2GHz

·LOW INTERMODULATION DISTORTION

IM3(MIN.) = -42dBc at Pout= 36.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.5A f= 6.4 to 7.2GHz	dBm	47.0	48.0	
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.5	7.5	
Drain Current	IDS1		А		13.2	15.0
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%		39	
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 36.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	_
Drain Current	IDS2		А			11.8
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C			100

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 12.0A	S	_	20	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 200mA	V	-1.0	-1.8	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	38	_
Gate-Source Breakdown Voltage	VGSO	IGS= -1.0mA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.6	0.8

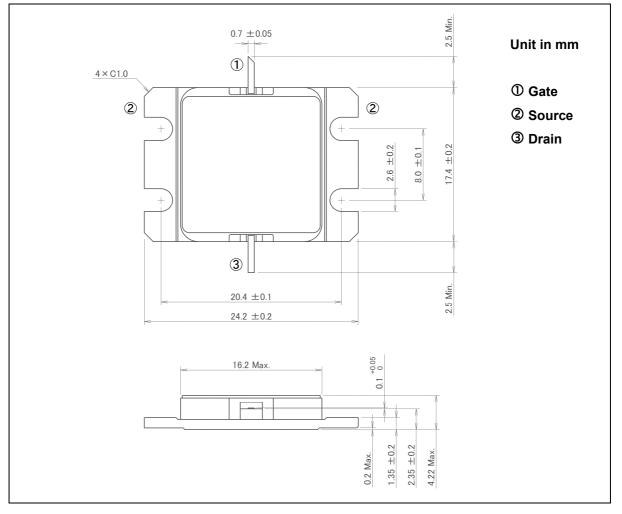
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

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CHARACTERISTICS	SYMBOL	UNIT	RATING			
Drain-Source Voltage	VDS	V	15			
Gate-Source Voltage	VGS	V	-5			
Drain Current	IDS	А	20			
Total Power Dissipation (Tc= 25°C)	PT	W	187.5			
Channel Temperature	Tch	°C	175			
Storage Temperature	Tstg	°C	-65 to +175			

PACKAGE OUTLINE (2-16G1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

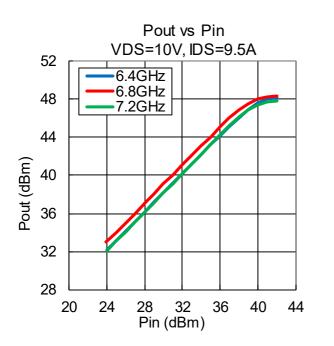
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

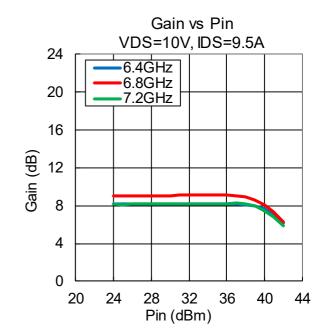
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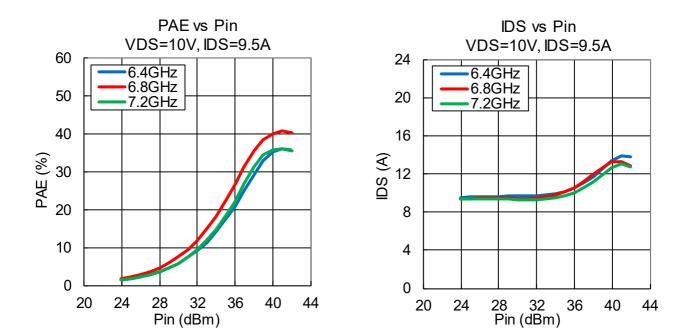
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 9.5 A, f= 6.4, 6.8, 7.2 GHz, Ta= +25 °C



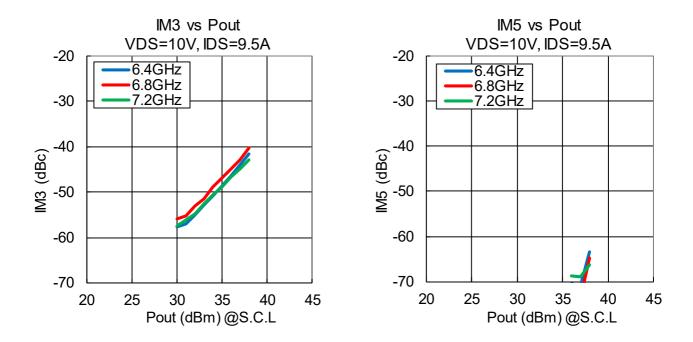




MICROWAVE SEMICONDUCTOR TECHNICAL DATA

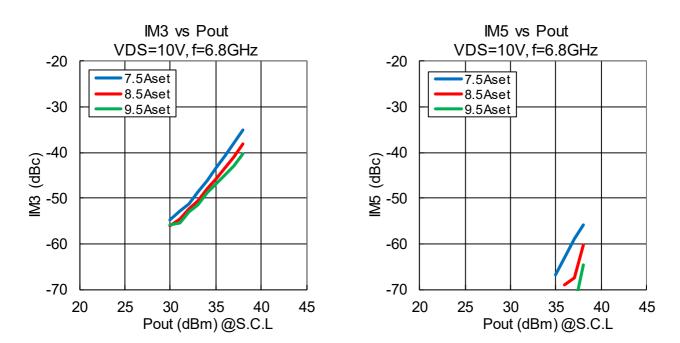
·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 9.5 A, f= 6.4, 6.8, 7.2 GHz, Δf= 5 MHz , Ta= +25 °C





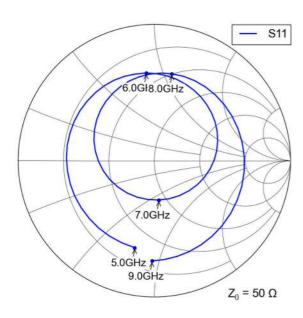
VDS= 10 V, f= 6.8 GHz, IDSset= 7.5A, 8.5A, 9.5A, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C

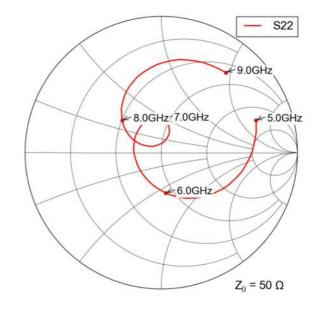


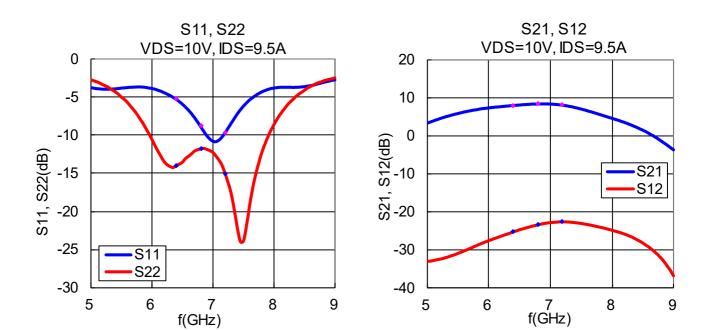
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·S-Parameters

VDS= 10 V, IDSset= 9.5 A, f= 5.0 to 9.0 GHz, Ta= +25 ℃







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